

TRANSMITTAL MESSAGE COVER SHEET

DATE: September 4, 2002

Please deliver the following pages to:

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MESSAGE:Re: U.S. Serial No. 09/416,959

Dear Examiner Pompey:

Enclosed please find a copy of the Amendment which we filed on September 3, 2002 regarding the above matter. I will look forward to discussing this amendment with you during our interview tomorrow afternoon.

TOTAL NUMBER OF PAGES INCLUDING COVER SHEET: 12

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501.35437CV2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: YOSHIDA et al.
Serial No.: 09/416,959
Filed: October 13, 1999
For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
AND PROCESS FOR MANUFACTURING THE SAME
Group: 2812
Examiner: R. Pompey

AMENDMENT

Assistant Commissioner
for Patents
Washington, D.C. 20231

September 3, 2002

Sir:

In response to the Office Action dated April 2, 2002, the period of response for which extension is requested by the attached Petition for Extension of Time, please amend the above-identified application as follows:

In the Claims:

Please cancel claims 18-41 without prejudice.

Please add new claims 42-49 as follows:

— 42. A semiconductor integrated circuit device having a first portion for a memory array and a second portion for a circuit other than the memory array on a semiconductor substrate comprising:

a MISFET arranged in said first portion, said MISFET having first semiconductor regions and a gate electrode between said first semiconductor regions;